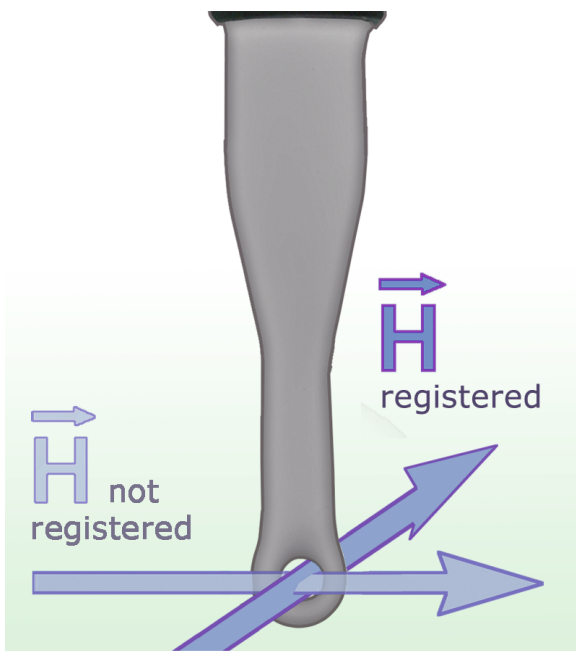


XF-R 3-1

H-Field Probe 30 MHz up to 6 GHz



Short description

The XF-R 3-1 near-field probe is designed for direct high-resolution measurements of RF magnetic fields on an assembly, e.g. around the pins and IC cases, conducting paths, decoupling capacitor, and EMC components.

In principle the XF-R 3-1 H-field probe has the same structure as the XF-R 100-1 and XF-R 400-1 probes. The resolution of the XF-R 3-1 is significantly higher. The H-field probe is suitable for measurements close to the components with high magnetic field strength. It is not suitable for measurements from large distances, which can be done using XF-R 400-1 and XF-R 100-1. The near-field probe is small and handy. It has a current attenuating sheath and, therefore, is electrically shielded. It can be connected to a spectrum analyzer or an oscilloscope with a 50 Ω input. The H-field probe has an internal terminating resistance.

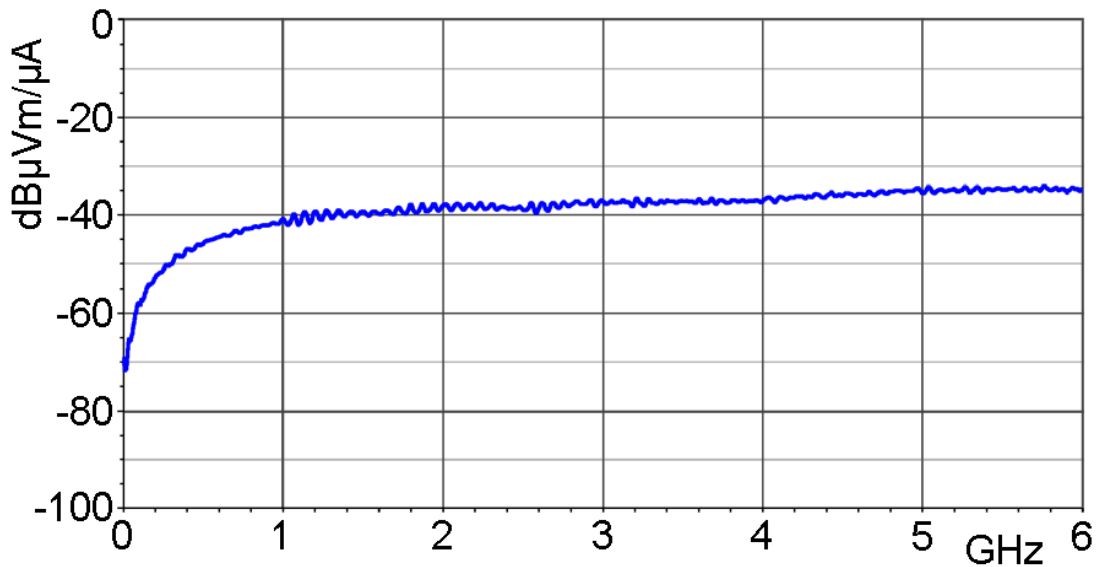
Technical parameters

| | |
|-----------------------|----------------------------|
| Frequency range | 30 MHz ... 6 GHz |
| Resolution | ≈ 1 mm |
| Probe head dimensions | $\varnothing \approx 3$ mm |
| Connector - output | SMA, female, jack |
| Weight | 15 g |

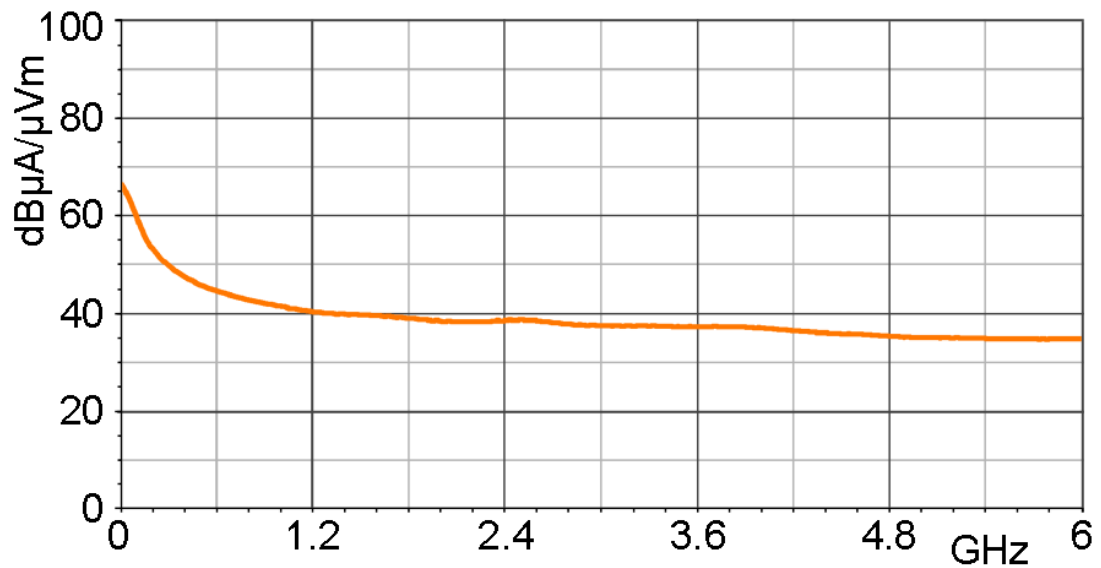
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Frequency response [dB μ V] / [dB μ A/m]



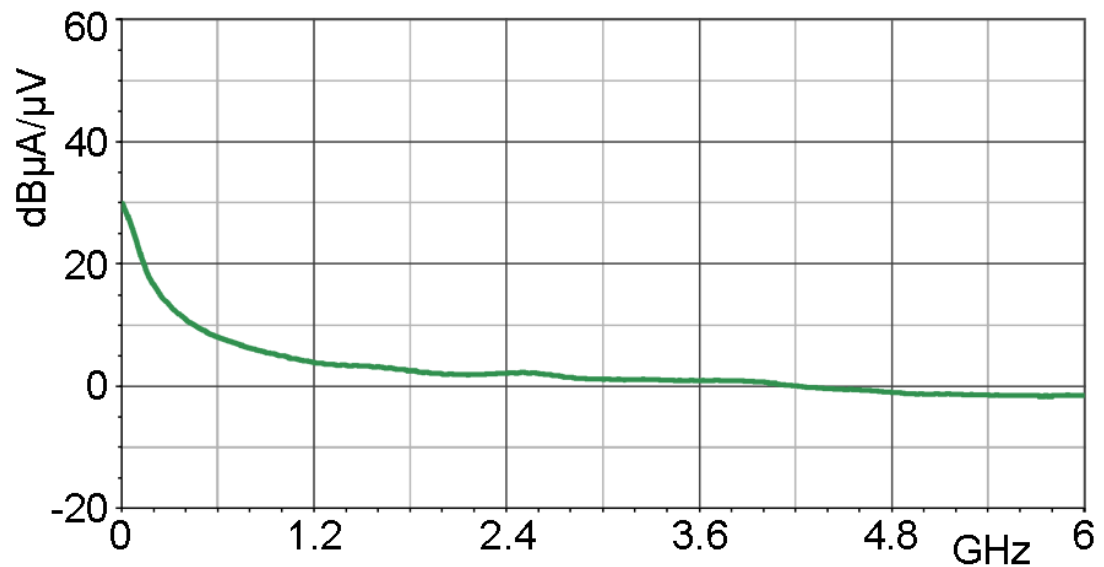
H-field correction curve [dB μ A/m] / [dB μ V]



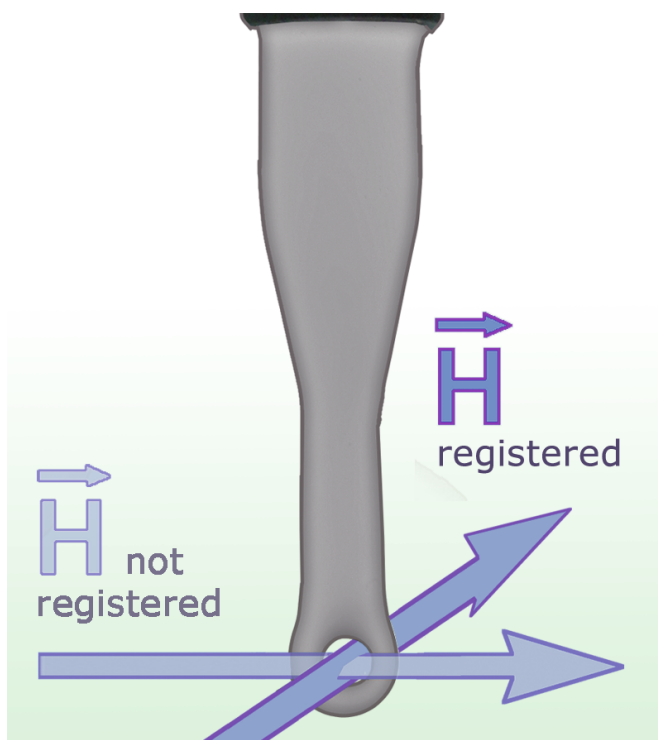
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Current correction curve [dB μ A] / [dB μ V]



Measuring principles



XF-R 3-1

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Probe head

